HD14007UB

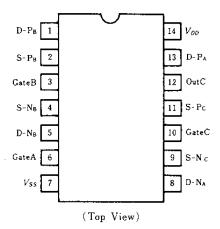
Dual Complementary Pair plus Inverter

The HD14007UB multi-purpose device consists of three N-channel and three P-channel enhancement mode devices packaged to provide access to each device. These versatile parts are useful in inverter circuits, pulse-shapers, linear amplifiers, high input impedance amplifiers, threshold detectors, transmission gating, and functional gating.

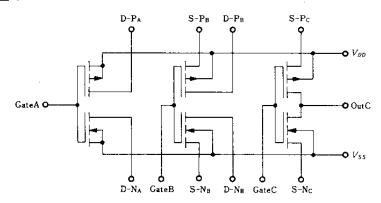
FEATURES

- Quiescent Current = 0.5nA/pkg typ @5V
- Supply Voltage Range = 3 to 18V
- Pin-for-Pin Replacement for CD4 007UB and MC14007UB

■ PIN ARRANGEMENT

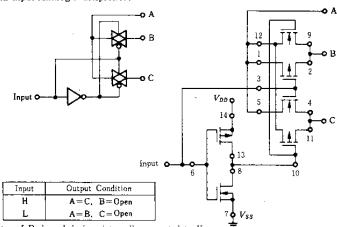


■ CIRCUIT SCHEMATIC



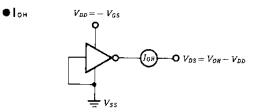
TYPICAL APPLICATION

(2-input Analog Multiplexer)

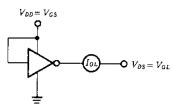


Substrates of P-channel devices internally connected to V_{DB} . Substrates of N-channel devices internally connected to V_{SS} .

MDC CHARACTERISTIC TEST CIRCUIT



All unused inputs connected to ground.



All unused inputs connected to ground.

● lou

EELECTRICAL CHARACTERISTICS

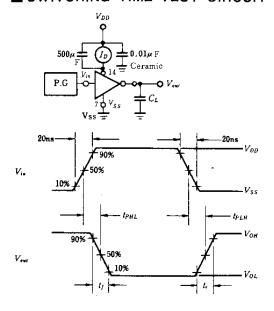
Characteristic	Symbol	Test Conditions		40°C		25°C			85℃		Unit
	O J III DO I	$V_{DD}(\mathbf{V})$	- Control Control Control	min	max	min	typ	max	min	max	
		5.0			0.05	_	0	0.05	-	0.05	v
	Vol	10	$V_{in} = V_{DD}$ or 0		0.05	-	0	0.05	_	0.05	
Output Voltage	i	15		_	0.05		0	0.05		0.05	
Output Voltage		5.0	$V_{in}\!=\!0$ or V_{DD}	4.95	_	4.95	5.0	_	4.95		· v
	V _{OH}	10		9.95		9.95	10		9.95	_	
		15		14.95	_	14.95	15		14.95	_	
'*		5.0	$V_{out} = 4.5 \text{ or } 0.5 \text{ V}$		1.0	_	2.25	1.0		1.0	v
	VIL	10	$V_{out} = 9.0 \text{ or } 1.0 \text{ V}$		2.0	_	4.50	2.0		2.0	
Input Voltage		15	$V_{out} = 13.5 \text{ or } 1.5 \text{ V}$	_	2.5		6.75	2.5	_	2.5	
mput voltage		5.0	$V_{out} = 0.5 \text{ or } 4.5 \text{ V}$	4.0	_	4.0	2.75	_	4.0	_	· v
	ViH	10	$V_{out} = 1.0 \text{ or } 9.0 \text{ V}$	8.0		8.0	5.50	_	8.0		
		15	$V_{out} = 1.5 \text{ or } 13.5 \text{ V}$	12.5	_	12.5	8.25	_	12.5		
	Іон	5.0	$V_{OH} = 2.5 \text{V}$	-1.3	_	-1.1	-5.0	_	-0.9		mА
		10	$V_{OH} = 9.5V$	-0.65		-0.55	-2.5	_	-0.45		
		15	$V_{OH} = 13.5 \text{V}$	-2.4	_	-2.0	-10	_	-1.6	_	
Output Drive Current	IoL	5.0	$V_{OL} = 0.4 \text{V}$	0.52	_	0.44	1.0	_	0.36		mA
		10	$V_{OL} = 0.5 V$	1.3		1.1	2.5	_	0.9	_	
		15	$V_{OL} = 1.5V$	4.0		3.3	10		2.7	_	
Input Current	Iin	15		-	± 0.3	_	±0.00001	±0.3	_	±1.0	μA
Input Capacitance	Cin	i	$V_{in}=0$	-	_	_	5.0	7.5	_		pF
Quiescent Current	I_{DD}	5.0		1 —	0.5	_	0.0005	0.5	.—	3.8	μA
		10	Zero Signal,		1.0	. —	0.0010	1.0	· —	7.5	
		15	per Package		2.0	_	0.0015	2.0	-	15	
Total Supply Current*	Ιτ	5.0	Dynamic+Ivo,	<u> </u>	_	_	0.72		_	_	μA
		10	per Gate,	-	_		1.44	_	_		
		15	$C_L = 50 \text{pF}, f = 1 \text{kHz}$	_		_	2.16	_			

^{*} To calculate total supply current at frequency other than 1kHz.

ESWITCHING CHARACTERISTICS $(C_L = 50 \text{pF}, Ta = 25^{\circ}\text{C})$

Characteristic	Symbol	$V_{DD}(V)$	typ	max	Unit	
		5.0	90	180		
Output Rise Time	t _r	10	45	90	ns	
		15	35	70		
	tf	5.0	75	150	ns	
Output Fall Time		10	40	80		
		15	30	60		
	tPLH	5.0	60	130	ns	
		10	30	75		
December Delay Time		15	25	55		
Propagation Delay Time		5.0	60	130		
	tphl	10	30	75	ns	
		15	25	55		

■ SWITCHING TIME TEST CIRCUIT



 $[@]V_{DD} = 5.0 \text{V} I_T = (0.72 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (1.44 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 15 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f + I_{DD}, \\ @V_{DD} = 10 \text{V} I_T = (2.16 \mu \text{ A/kHz}) f +$

DC CHARACTERISTICS ($V_{CC}=5V\pm10\%$, Ta=-40 to $+85^{\circ}C$)

Item	Symbol	Test Condition		min	typ	max	Unit
I W-14	V_{IH}	$V_{\text{pul}} = 0.1 \text{V or } V_{\text{CC}} = 0.1 \text{V},$	2.0		_	V	
Input Voltage	V_{tL}	<i>I</i> _{out} ≤20μA		_	_	0.8	V
O V h	V_{OH}	I/ I/ I/ I/ O04	$V_{cc} = 0.05$	Vcc		V	
Output Voltage	Vol	$V_{in} = V_{IH} \text{ or } V_{IL}, I_{out} \leq 20 \mu A$	_	0.0	0.05	V	
0	Іон	$V_{in} = V_{IH}$ or V_{IL} , $V_{out} = V_{CC} - 0$			-6.0	mA	
Output Current	Ioz	$V_{I\pi} = V_{IH}$ or V_{IL} , $V_{out} = 0.4 \mathrm{V}$		6.0		_	mA
Input Current	Iia	$V_{is} = V_{CC}$ or GND		_	±0.00001	±1.0	μA
3-state Leakage Currënt	7		<i>Ta</i> = 25°C			0.5	μA
	I_{TL}		<i>Ta</i> =85°C			5.0	μA
Quiescent Current	Icc	$V_{in} = V_{CC}$ or GND,	<i>Ta</i> − 25°C			4.0	μA
		$I_{out} = 0 \mu A$	<i>Ta</i> = 85°C			40	μA

■AC CHARACTERISTICS (V_{cc} =5V, T_a =25°C, Input t_r = t_f =6ns)

Item	Symbol	Test Condition	min	typ	max	Unit
Maximum Clock Frequency	f_{\max}	C _L =50pF			30	MHz
Propagation Delay Time	t _{PLH}	$C_{\perp} = 50 \mathrm{pF}$	_		.28	ns
Output Enable Time	tzL	C 50 F B 110	_	-	30	
	ŧzн	$C_L = 50 \text{pF}, R_L = 1 \text{k}\Omega$		_	30	ns
Output Disable Time	tız	C FO E B 110		_	25	
	t _{HZ}	$C_L = 50 \text{pF}, R_L = 1 \text{k}\Omega$	_	_	25	ns
Setup Time	t su		20	_	_	ns
Hold Time	t h		_	_	_	ns
Pulse Width	ŧ w		16	_	_	ns
Input Capacitance	C_{in}			· —	10	рF

Switching Waveforms

Figure 1

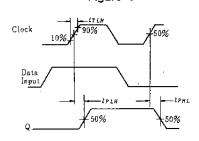


Figure 2a

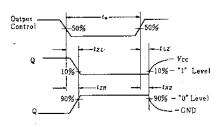
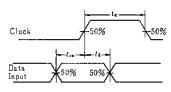


Figure 2b - Load Circuit for Three-State Outputs

From $R_L = 1 k \Omega$ $V_{CC}(t_{LZ}, t_{ZL})$ Under Test $C_L = 50 \text{pF GND}(t_{HZ}, t_{ZH})$

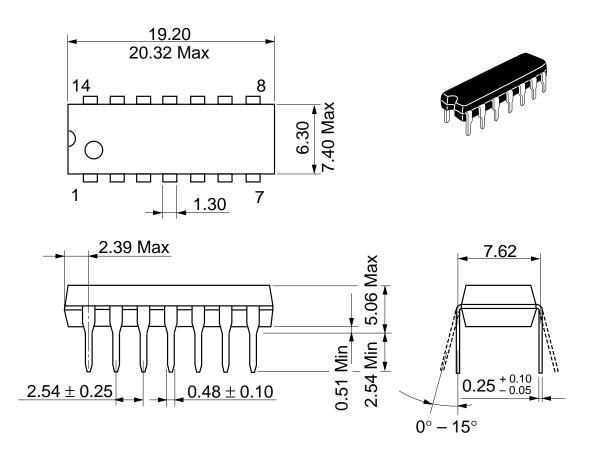
Figure 3



^{*}Outputs Q shown are for the HCT374. Outputs for the HCT534 are the inversion of those for the HCT374.



Unit: mm



Hitachi Code	DP-14
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.97 g

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